

Ximeng Guan

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EDUCATION

- Sept. 2005 – present **Tsinghua University**, China
Ph. D. candidate at the Institute of Microelectronics.
Area of research: semiconductor device modeling and simulation
Expected graduation date: July, 2010.
- Jan. – Aug. 2008 **Stanford University**, U.S.
Visiting researcher at the Center for Integrated Systems
<http://nano.stanford.edu/members.php>
- Sept. 2001– Jul. 2005 **Tsinghua University**, China
B.E. degree from Department of Electronic Engineering
GPA: 90.2/100 Rank: 5/164.

EXPERIENCES:

- Jul. 2006 – Jul. 2007 Vice chair, IEEE student branch ED chapter in Tsinghua
- Jul. 2006 – Oct. 2006 Intern student, Intel China Ltd. Beijing Branch, programming for transistor modeling and simulation.
- Jul. 2005 – Jul. 2006 Vice chair, IEEE student branch in Tsinghua

HONORS/AWARDS

- Dec. 2009 [IEEE Electron Device Society PhD Student Fellowship](#)
- Jan. 2007 Chenming Hu Scholarship for outstanding research and school performance
- Nov. 2005 Second-place Prize for Intel's High Performance Computation and Optimization Contest in China
- Jul. 2005 Graduate with honor (57 out of 3801), Honeywell Scholarship for overall merit
- 2001-2005 Scholarship for excellent curricular performance every year, Tsinghua University

SKILL SETS:

- Languages:** English, Chinese. **Programming:** C, CUDA, MATLAB, Bash.
- Computer Experience:** Linux, Solaris, Windows, MS Office, LaTeX, MS Visual Studio 6.0, OpenMP/MPI, Intel ICC/vTune/MKL/Thread Profiler, HSPICE, Cadence SpectreRF/Virtuoso, DESSIS.

SELECTED PUBLICATIONS¹:

- [1] **Ximeng Guan**, Yu He, Liang Zhao, Jinyu Zhang, Yan Wang, He Qian, and Zhiping Yu, "Simulation Study of Switching Mechanism in Carbon-Based Resistive Memory with Molecular Dynamics and Extended Hückel Theory-Based NEGF Method," International Electron Devices Meeting (**IEDM**), Baltimore, MD, USA, Dec. 7-9, 2009 (to be presented).
- [2] **Ximeng Guan**, Qiushi Ran, Ming Zhang, Zhiping Yu, and H.-S. Philip Wong, "Modeling of Schottky and ohmic contacts between metal and graphene nanoribbons using extended Haeckel theory-based (EHT) NEGF Method," International Electron Devices Meeting (**IEDM**) Tech. Dig., pp. 197-200, San Francisco, CA, USA, Dec. 14-17, 2008. [[PDF](#)]
- [3] **Ximeng Guan**, Ming Zhang, and Zhiping Yu, "Surviving process variation: Investigation of CNR MOSFETs with tapered channels using fully self-consistent NEGF and tight-binding methods," IEEE Electron Device Letters (**IEEE EDL**) Vol. 29, Issue 7, pp. 759-761, 2008. [[PDF](#)]
- [4] **Ximeng Guan**, Ming Zhang, Qiang Liu, and Zhiping Yu, "Simulation investigation of double-gate CNR-MOSFETs with a fully self-consistent NEGF and TB method," International Electron Devices Meeting (**IEDM**) Tech. Dig., pp. 761-764, Washington D.C., USA, Dec. 10-12, 2007. [[PDF](#)]
- [5] **Ximeng Guan**, Yaohua Tan, Jing Lu, Yan Wang, and Zhiping Yu, "A self-consistent simulation of InSb double-gate MOSFETs using full-band tight-binding approach," **SISPAD** Proc. pp. 161-164, Vienna, Austria, Sept. 25-27, 2007. [[PDF](#)]

¹ Full publication list available at <http://www.net-glyph.org/~guanxm/>